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June 2014



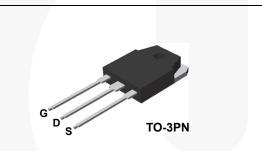
FQA24N60 N-Channel QFET[®] MOSFET 600 V, 23.5 A, 240 mΩ

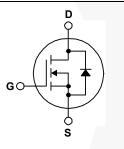
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- + 23.5 A, 600 V, $R_{DS(on)}$ = 240 m Ω (Max.) @ V_{GS} = 10 V, I_{D} = 11.8 A
- Low Gate Charge (Typ. 110 nC)
- Low Crss (Typ. 56 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

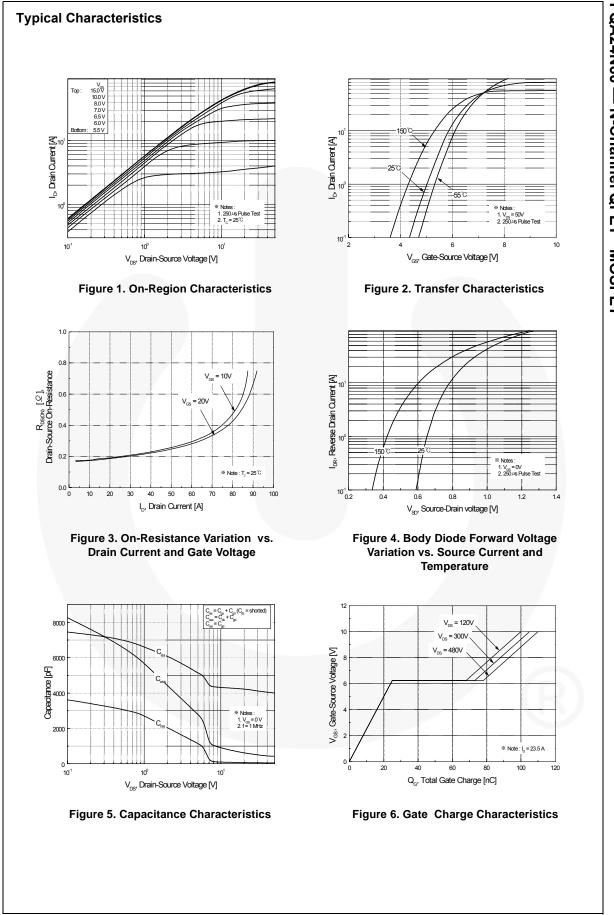
| Symbol | Parameter | FQA24N60 | Unit | |
|-----------------------------------|--|-------------|------|------|
| V _{DSS} | Drain-Source Voltage | 600 | V | |
| I _D | Drain Current - Continuous ($T_C = 25^{\circ}C$) | 23.5 | A | |
| | - Continuous (T _C = 100°C | 14.9 | A | |
| DM | Drain Current - Pulsed | (Note 1) | 94 | A |
| V _{GSS} | Gate-Source Voltage | ± 30 | V | |
| AS | Single Pulsed Avalanche Energy | (Note 2) | 1300 | mJ |
| AR | Avalanche Current | (Note 1) | 23.5 | A |
| E _{AR} | Repetitive Avalanche Energy | (Note 1) | 31 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 4.5 | V/ns |
| D | Power Dissipation (T _C = 25°C) | | 310 | W |
| | - Derate above 25°C | 2.5 | W/°C | |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55 to +150 | | |
| Γ _L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300 | °C | |

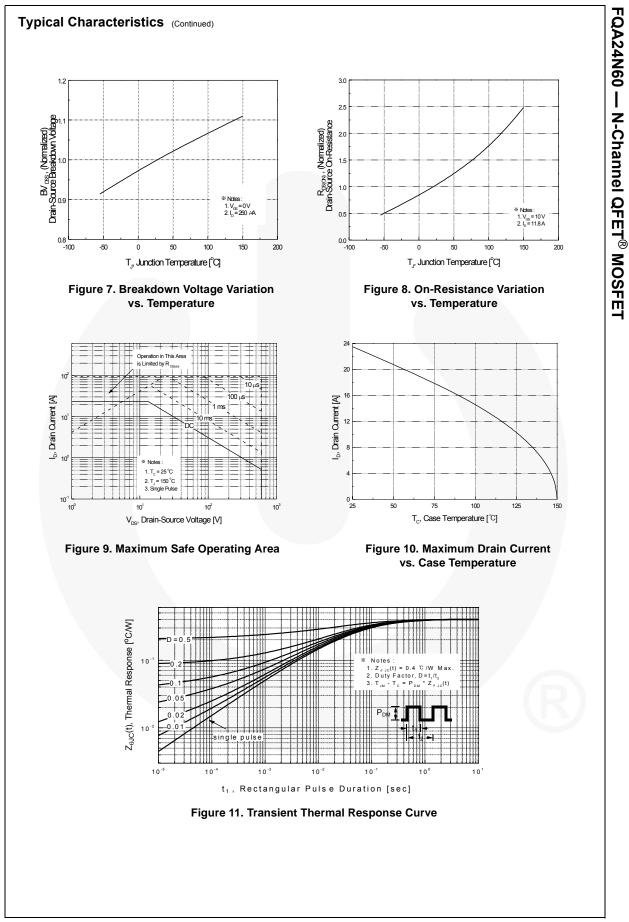
Thermal Characteristics

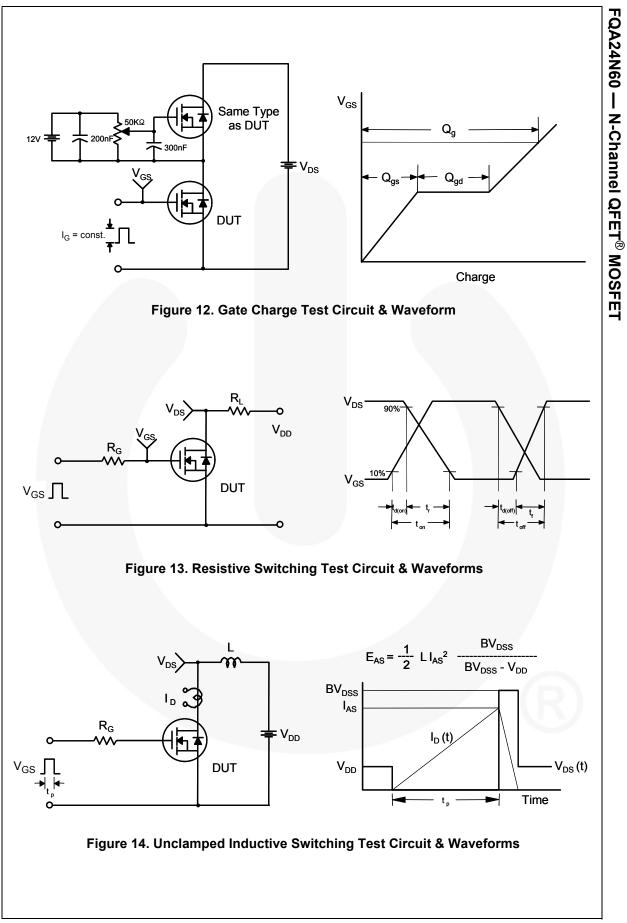
| Symbol | Parameter | FQA24N60 | Unit |
|---------------------|---|----------|------|
| $R_{	ext{	heta}JC}$ | Thermal Resistance, Junction-to-Case, Max. | 0.4 | °C/W |
| $R_{\theta CS}$ | Thermal Resistance, Case-to-Sink, Typ. | 0.24 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 40 | °C/W |

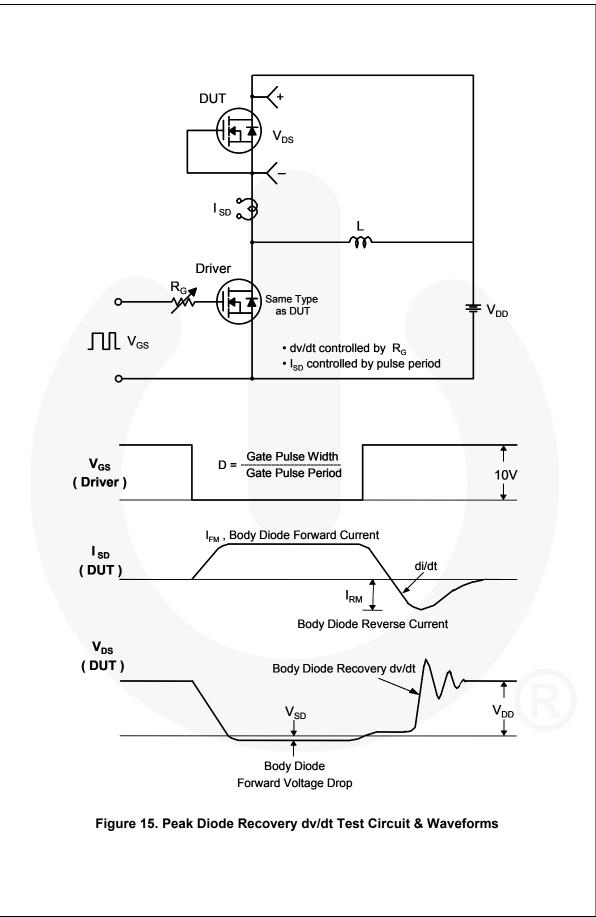
| Symbol Off Cha BV _{DSS} ΔBV _{DSS} (ΔT _J | cal Cha racteris | FQA24N60 | | age | Packing Method | Reel S | Size | Tape W | Mun | Quantity |
|---|--|---|---|---|---|----------|----------|-----------|------------|----------|
| Symbol Off Cha BV _{DSS} ΔBV _{DSS} / ΔT _J | racteris Drain-So | aracteristics | TO-3 | | | N// | Ą | N/A | | 30 units |
| Symbol Off Cha BV _{DSS} ΔBV _{DSS} / ΔT _J | racteris Drain-So | | T. = 25°C un | less otherwi | se noted | | | | | |
| Off Cha BV _{DSS} ΔBV _{DSS} / ΔT _J I _{DSS} | Drain-So | Parameter | 1 _C 200 an | | Test Conditions | | Min. | Тур. | Max. | Unit |
| BV _{DSS} ΔBV _{DSS} / ΔT _J | Drain-So | | | | | | | | | - |
| ΔBV _{DSS} / ΔT _J | | ource Breakdown Vol | ade | V _{GS} = (| Ο V, I _D = 250 μA | | 600 | | | V |
| $/\Delta T_{J}$ | Breakdov | down Voltage Temperature | | | | | | | | |
| Ince | Coefficient | | $I_D = 250 \ \mu$ A, Referenced to 25°C | | | 0.6 | | V/°C | | |
| .035 | Zero Gate Voltage Drain Current | | _ | $500 \text{ V}, \text{ V}_{\text{GS}} = 0 \text{ V}$ | | | | 10 | μA | |
| | | | | $V_{DS} = 480 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$ | | | | | 100 | μΑ |
| I _{GSSF} | | dy Leakage Current, | | | $30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$ | | | | 100 | nA |
| I _{GSSR} | Gate-Boo | dy Leakage Current, | Reverse | V _{GS} = - | $-30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$ | | | | -100 | nA |
| On Cha | racteris | tics | | | | | | | | |
| V _{GS(th)} | Gate Thr | reshold Voltage | | V _{DS} = | V _{GS} , I _D = 250 μA | | 3.0 | | 5.0 | V |
| R _{DS(on)} | | ain-Source | | V _{GS} = | 10 V, I _D = 11.8 A | | | 0.18 | 0.24 | Ω |
| 9 _{FS} | | Dn-Resistance Forward Transconductance | | V _{DS} = 50 V, I _D = 11.8 A | | | | 22.5 | | S |
| Dvnami | c Chara | acteristics | | | | | | | | |
| C _{iss} | | pacitance | | $V_{\rm DC} = 2$ | 25 V, V _{GS} = 0 V, | | | 4200 | 5500 | pF |
| C _{oss} | | apacitance | | f = 1.0 | | | | 550 | 720 | pF |
| C _{rss} | Reverse | Transfer Capacitanc | e | | | | | 56 | 75 | pF |
| | na Chai | ractoristics | | | | | | | | |
| | - | racteristics Delay Time | | | | | | 00 | 100 | |
| t _{d(on)} t _r | | Rise Time | | | $300 \text{ V}, \text{ I}_{\text{D}} = 23.5 \text{ A},$ | | | 90 270 | 190 550 | ns |
| | | Delay Time | | R _G = 2 | 5 7 2 | | | 200 | 410 | ns |
| t _{d(off)} t _f | | Fall Time | | | | (Note 4) | | 170 | 350 | - |
| Qg | | te Charge | | V - | 190 \/ = 22 E A | | | 110 | 145 | ns |
| Q _{gs} | | urce Charge | | $V_{DS} = 2$ $V_{GS} = 2$ | 480 V, I _D = 23.5 A, | | | 25 | | nC |
| | Gale-50 | | | VGS - | | (Note 4) | | 53 | | nC |
| - | Gate_Dra | an charge | | | | (, | - | - 55 | | ne |
| Q _{gd} | Gate-Dra | | | | | | | | | |
| Q _{gd} Drain-Se | ource D | oiode Character | | | 0 | | 1 | 1 | | |
| Q _{gd} Drain-So | ource D Maximur | n Continuous Drain-S | Source Dic | de Forwa | ard Current | | | | 23.5 | Α |
| Q _{gd} Drain-So I _S I _{SM} | ource D Maximun Maximun | n Continuous Drain-S n Pulsed Drain-Sourc | Source Dic ce Diode F | de Forward C | ard Current | | | | 23.5 94 | Α |
| Q _{gd} Drain-So I _S I _{SM} V _{SD} | ource D Maximun Maximun Drain-So | n Continuous Drain-S n Pulsed Drain-Sourd purce Diode Forward | Source Dic ce Diode F | ode Forward C Forward C V _{GS} = 0 | ard Current Current O V, I _S = 23.5 A | | | | | |
| Q _{gd} | ource D Maximur Maximur Drain-So Reverse | n Continuous Drain-S n Pulsed Drain-Sourc | Source Dic ce Diode F | ode Forward C Forward C $V_{GS} = 0$ $V_{GS} = 0$ | ard Current | | | | 94 | Α |

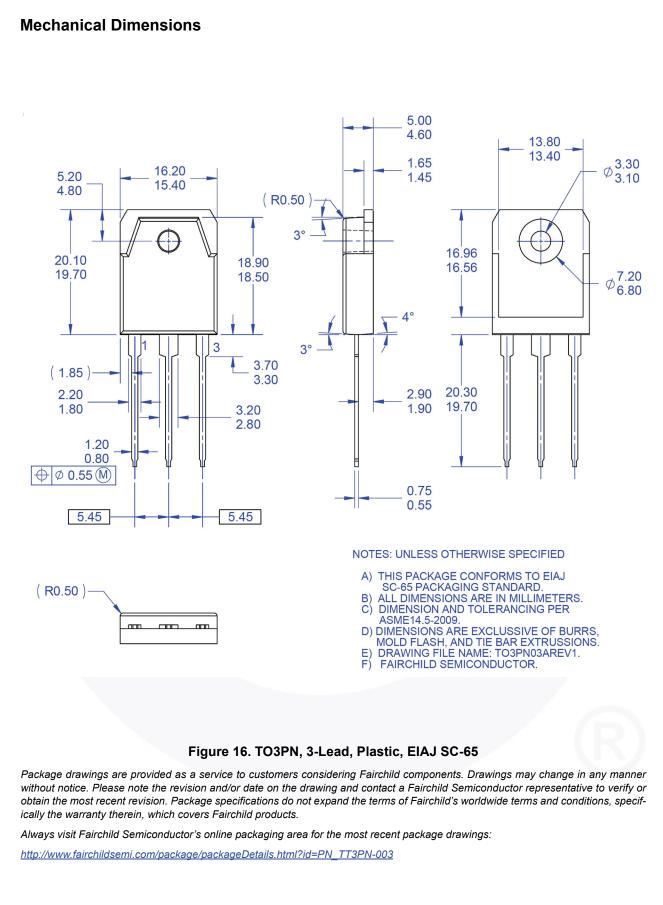
FQA24N60 — N-Channel QFET[®] MOSFET













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|--------------------------|-----------------------|---|--|--|--|
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